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TSM60NB900CP ROG

TSM60NB900CP ROG Information

Part Number TSM60NB900CP ROG Manufacturer TSC America Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET, SINGLE, N-CHANNEL, SUPER**Package**TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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TSM60NB900CP ROG Specifications

| Manufacturer Part Number TSM60NB900CP ROG Manufacturer TSC America Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 9.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 315pF @ 100V Vgs (Max) Vgs (Max) Vgs (Max) 0V Vgs (Max) 90 Mov PET Feature - Power Dissipation (Max) 36.8W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC | | |
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| FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds315pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)36.8W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63 | Package | TO-252-3, DPak (2 Leads + Tab), SC-63 |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds315pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)36.8W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63 | Series | - |
| Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds315pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)36.8W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63 | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.2A, 10V Operating Temperature Surplier Device Package TO-252, (D-Pak) Package / Case 4A (Tc) 4V @ 250μA 315pF @ 100V 430V FET Feature | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs9.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds315pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)36.8W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63 | Drain to Source Voltage (Vdss) | 600V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-252-3, DPak (2 Leads + Tab), SC-63 | Current - Continuous Drain (Id) @ 25°C | 4A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs 9.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 315pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 36.8W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Vgs(th) (Max) @ Id | 4V @ 250μA |
| Vgs (Max)±30VFET Feature-Power Dissipation (Max)36.8W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63 | Gate Charge (Qg) (Max) @ Vgs | 9.6nC @ 10V |
| FET Feature - Power Dissipation (Max) 36.8W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Input Capacitance (Ciss) (Max) @ Vds | 315pF @ 100V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 1.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Vgs (Max) | ±30V |
| Rds On (Max) @ Id, Vgs900 mOhm @ 1.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-252, (D-Pak)Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63 | FET Feature | - |
| Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Power Dissipation (Max) | 36.8W (Tc) |
| Mounting Type Surface Mount TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Rds On (Max) @ Id, Vgs | 900 mOhm @ 1.2A, 10V |
| Supplier Device Package TO-252, (D-Pak) Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Operating Temperature | -55°C ~ 150°C (TJ) |
| Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 | Mounting Type | Surface Mount |
| | Supplier Device Package | TO-252, (D-Pak) |
| Report errors? | Package / Case | TO-252-3, DPak (2 Leads + Tab), SC-63 |
| | | Report errors? |

TSM60NB900CP ROG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

TSM60NB900CP ROG Payment Methods



















TSM60NB900CP ROG Shipping Methods













If you have any question about TSM60NB900CP ROG, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com